

AMENDMENTS TO THE SPECIFICATION

- Please insert the following section to the specification which begins on page 1, line 2, as follows:

CROSS REFERENCE TO RELATED APPLICATIONS

This is a divisional of co-pending application serial number 10/128,771, filed on April 22, 2002.

- Please amend the Title which begins on page 1, line 1, as follows:

METHOD OF MANUFACTURING A SEMICONDUCTOR MEMORY
WITH DEUTERATED MATERIALS

- Please amend the Disclosure of the Invention section, which begins on page 3, line 7, as follows:

DISCLOSURE OF THE INVENTION

The present invention provides a manufacturing method for a MirrorBit® Flash memory and includes providing a semiconductor substrate and successively depositing a first insulating layer, a charge-trapping layer, and a second insulating layer. First and second bitlines are implanted and wordlines are formed before completing the memory. Spacers are formed between the wordlines and an inter-layer dielectric layer is formed over the wordlines. One or more of the second insulating layer, wordlines, spacers, and inter-layer dielectric layer are deuterated, replacing hydrogen bonds with deuterium, thus improving data retention and substantially reducing charge loss.

~~The present invention also provides a MirrorBit® Flash memory including a semiconductor substrate with a first insulating layer, charge trapping layer, and a second insulating layer deposited thereon. First and second bitlines are implanted and wordlines are formed over the second insulating layer. Spacers are formed between the wordlines and an~~

~~inter-layer dielectric layer is formed over the wordlines. One or more of the second insulating layer, wordlines, spacers, and inter-layer dielectric layer are deuterated, replacing hydrogen bonds with deuterium, thus improving data retention and substantially reducing charge loss.~~

The above and additional advantages of the present invention will become apparent to those skilled in the art from a reading of the following detailed description when taken in conjunction with the accompanying drawings.

- Please amend the Abstract which begins on page 13, line 1, as follows which begins on the next page: